HFZT

PXT3906

SOT-89 Plastic-Encapsulate Transistors

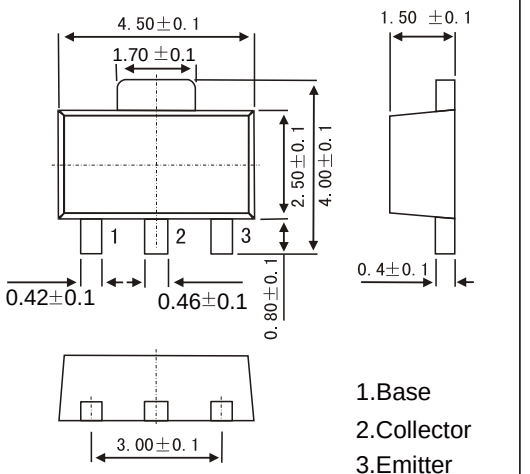
Features

- Collector Current Capability IC=-0.2A
- Collector Emitter Voltage VCEO=-40V
- Compliment to PXT3904
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

SOT-89 Unit:mm



1.Base
2.Collector
3.Emitter

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-40	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E= 0	-40			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B= 0	-40			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μA, I_C= 0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E= 0			-50	nA
Collector- emitter cut-off current	I_{CEX}	V_{CE}= -30 V , $V_{BE(off)}$= -3V			-50	
Emitter cut-off current	I_{EBO}	V_{EB}= -6V , I_C=0			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.25	V
		I_C=-50 mA, I_B=-5mA			-0.4	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA	-0.65		-0.85	
		I_C=-50 mA, I_B=-5mA			-0.95	
DC current gain	h_{FE}	V_{CE}= -1V, I_C= -0.1mA	60			
		V_{CE}= -1V, I_C= -1mA	80			
		V_{CE}= -1V, I_C= -10mA	100		300	
		V_{CE}= -1V, I_C= -50mA	60			
		V_{CE}= -1V, I_C= -100mA	30			
Noise figure	NF	V_{CE}=-5V,I_C=-0.1mA, f=10Hz-15.7kHz,R_S=1KΩ			4	dB
Delay time	t_d	I_C=-10mA , I_{B1}=-I_{B2}= -1mA			35	ns
Rise time	t_r				35	
Storage time	t_s				225	
Fall time	t_f				75	
Collector output capacitance	C_{ob}	V_{CB}= -5V, I_E= 0,f=1MHz			4.5	pF
Emitter capacitance	C_e	V_{EB}=-0.5V,I_C=0,f=1MHz			10	
Transition frequency	f_T	V_{CE}= -20V, I_C= -10mA,f=100MHz	250			MHz

■ Marking

Marking	2A